

**Amendments to the Claims**

1. (currently amended) A method of producing a template for oxygen precipitation in a semiconductor wafer in ~~[a housing which defines a process chamber having]~~ an apparatus comprising (i) a treating station for heating and/or depositing an epitaxial coating on said wafer, the treating station comprising a source of heat, and a wafer support, (ii) a holding station for holding a wafer and (iii) a Bernoulli wand operable to move a wafer from the treating station to the holding station, said method ~~[including]~~comprising:

heating a semiconductor wafer with opposite major surfaces in ~~at the process chamber~~ treating station to an elevated temperature of at least about 1175°C with ~~the a~~ heat source, said wafer being supported in immediate heat transfer relation with the ~~wafer~~ support in the ~~process-chamber~~ treating station during said heating;

ceasing said heating and moving said wafer out of conductive heat transfer relation with the support with the Bernoulli wand; and

cooling said heated wafer ~~in the process chamber in which the wafer was heated while holding said wafer out of conductive heat transfer relationship with the support~~ at a rate of at least ~~10°C/sec~~ 50°C/sec until the wafer reaches a temperature of less than about 850°C while the wafer is held by the Bernoulli wand, thereby forming a template for oxygen precipitation in the wafer.

2. (twice amended) A method as set forth in claim 1 wherein the process additionally comprises the step of placing the wafer in the ~~[housing]~~ treating station and applying an epitaxial coating to at least one said major surface thereof before said heating step with said wafer being in immediate heat transfer relation with the support during at least a portion of the coating application and without an intervening cooling step after said coating step and before said heating step.

3. (twice amended) A method as set forth in claim 2 wherein said wafer is heated to a temperature of at least about 1250°C after said coating is applied [and the cooling rate of the wafer is at least about 20°C/sec].

4-8. (cancelled)

9. (amended) A method as set forth in claim [6]1 wherein said cooling rate is at least about 50°C/sec until the temperature of the wafer is reduced at least about 325°C.

10-11. (cancelled)

12. (amended) A method as set forth in claim [6]1 wherein said cooling rate is at least about 50°C/sec until the temperature of the wafer is reduced at least about 400°C.

13-14. (cancelled)

15. (amended) A method as set forth in claim [6]1 wherein said cooling rate is at least about 50°C/sec until the temperature of the wafer is reduced at least about 450°C.

16. (original) A method as set forth in claim 1 wherein said heat source is light.

17. (original) A method as set forth in claim 16 wherein said heat source is a halogen lamp.

18-20. (cancelled).